



DWSUC0522N-Q ESD Protection Diode

Feature

- Bi-directional ESD protection of one line
- 100Watts peak pulse power ($t_p = 8/20\mu s$)
- Working voltage: 5V
- Junction Capacitance: 0.7pF(Typ)
- Low clamping voltage
- Low leakage current
- AEC-Q101 qualified
- IEC 61000-4-2 $\pm 25kV$ contact $\pm 25kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 7A (8/20 μs)

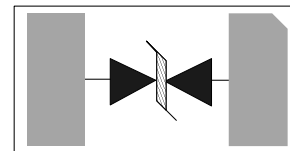
Application

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assestants(PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Data

- Package: DFN1006-2L
- Molding compound flammability rating: UL 94V-0
- RoHS/WEEE Compliant

Schematic & PIN Configuration



Ordering Information

Part Number	Package	Marking	Packing	Reel Size
DWSUC0522N-Q	DFN1006-2L	 UE	10000 Tape & Reel	7 inches



Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Units
Peak Pulse Power ($t_p=8/20\mu\text{s}$)	P_{PP}	100	Watts
Peak Pulse Current ($t_p=8/20\mu\text{s}$) (note1)	I_{PP}	7	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	± 25 ± 25	kV
Lead Soldering Temperature	T_L	260 (10seconds)	$^{\circ}\text{C}$
Junction Temperature	T_J	-55 to + 125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to + 125	$^{\circ}\text{C}$

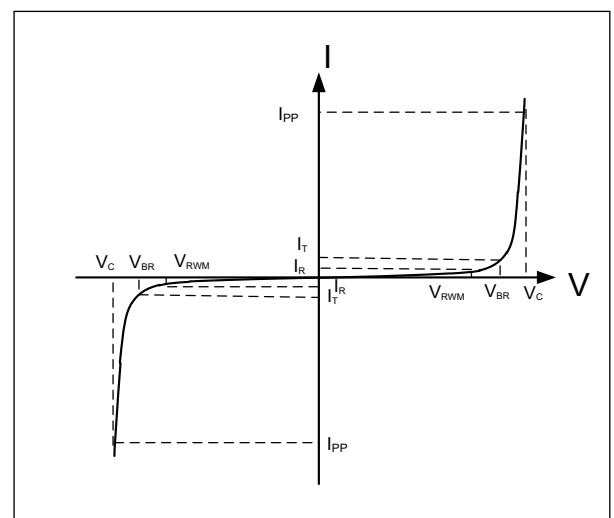
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	6.0	8.0		V
Reverse Leakage Current	I_R	$V_{RWM}=5\text{V}, T=25^{\circ}\text{C}$		0.1	0.5	μA
Clamping Voltage	V_C	$I_{PP}=7\text{A}, t_p=8/20\mu\text{s}$			16	V
Junction Capacitance	C_j	$V_R = 0\text{V}, f = 1\text{MHz}$		0.7	0.8	pF

Electrical Parameters

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

Note.: 8/20 μs pulse waveform.





Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

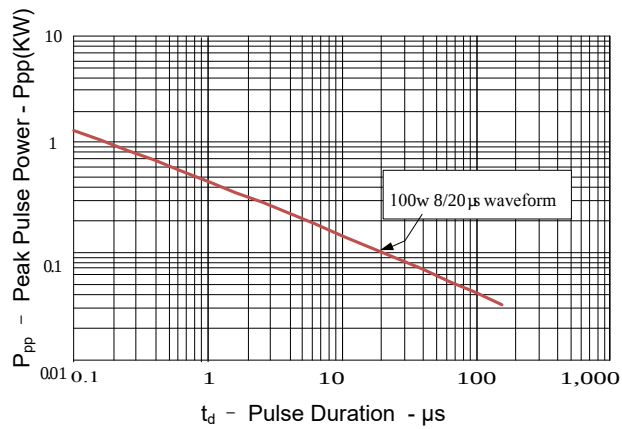


Figure 2: Power Derating Curve

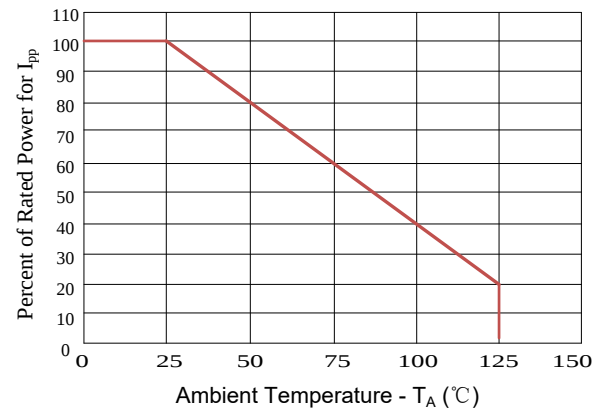


Figure3: Pulse Waveform

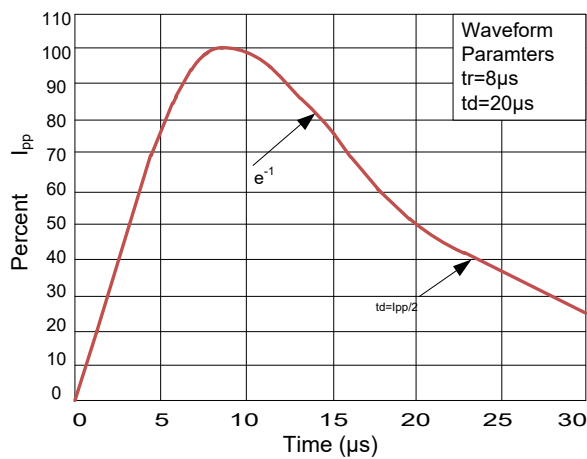
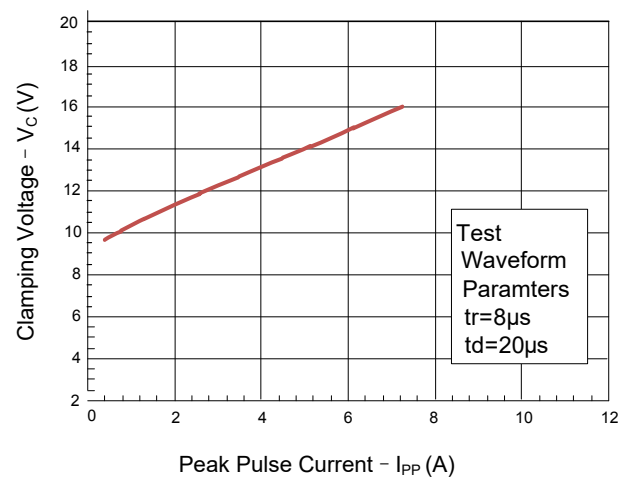
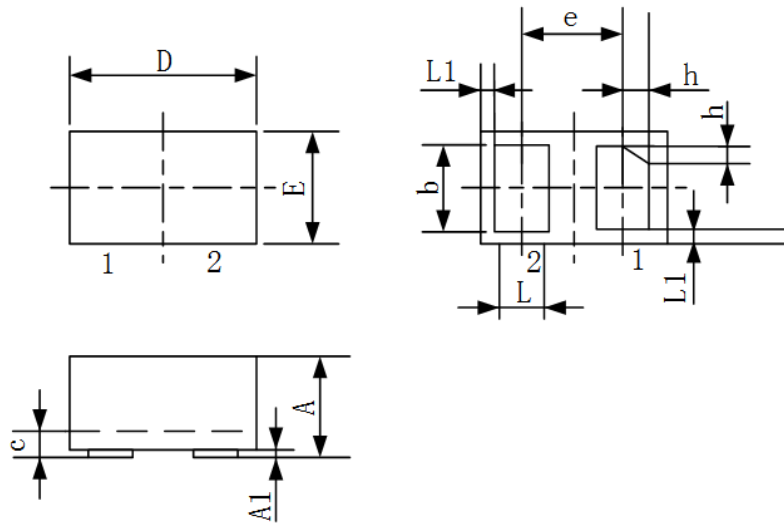


Figure 4: Clamping Voltage vs. I_pp





DFN1006-2L Outline Drawing



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.40	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
c	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17
载体尺寸 (MIL)	20*20		